

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	"10586810"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 11:07
S2	670	438/309.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 11:10
S3	8311	438/309-378.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 11:10
S4	10	US-5506427-\$.DID. OR US-5773350-\$.DID. OR JP-02203533-\$.DID. OR JP-02205033-\$.DID. OR US-1111142-\$. DID.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2009/04/29 12:01
S5	46205	(led or emitter or emitting) and (bipolar near2 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2009/04/29 12:09
S6	6515	((mono near2 (crystal or crystalline)) or monocrystalline or monocrystal or (single near2 (crystalline or crystal))) and (((silicon near2 (oxide or dioxide)) or "sio.sub.2" or sio2) same (sidewall or (side near2 wall))) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:12
S7	535	S5 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:12
S8	169	S7 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:12
S9	8131	((((mono near2 (crystal or crystalline)) or monocrystalline or monocrystal or (single near2 (crystalline or crystal)) or epitaxially or epitaxial) with (silicon or si)) and (((silicon near2 (oxide or dioxide)) or "sio. sub.2" or sio2) same (sidewall or (side near2 wall)))) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:13

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S10	63	"5506427"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:15
S11	51	"5773350"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:15
S12	6048	S9 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:25
S13	240	S12 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:25
S14	40684	((selective near2 epitaxial near2 growth) or SEG)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:30
S15	50	S13 and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 12:30
S16	63	"5506427"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 14:29
S17	51	"5773350"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 14:29
S18	110	(S16 or S17)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 14:29
S19	26	S18 and (DEG or (differential near2 (epitaxial or epitaxy) near2 (growth or grow or grown or growing)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 14:30

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S20	0	S18 and ((differential near2 (epitaxial or epitaxy) near2 (growth or grow or grown or growing)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 14:32
S21	20	((differential near2 (epitaxial or epitaxy) near2 (growth or grow or grown or growing)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 14:32
S22	2	"20070111485"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 14:50
S23	5	"2006114746"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 14:52
S24	31	"5506427" and (salicide or silicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 15:13
S26	9	"5506427" and ((salicide or silicide) same (ti or titanium or co or cobalt or ni or nickel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 15:15
S27	190	((differential or nonselective or (non near2 selective)) near2 (epitaxial or epitaxy) near2 (growth or grow or grown or growing)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 15:21
S28	148	((differential or nonselective or (non near2 selective)) near2 (epitaxial or epitaxy) near2 (growth or grow or grown or growing))) same (polysilicon or silicon or si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 15:23
S29	36	((differential or nonselective or (non near2 selective)) near2 (epitaxial or epitaxy) near2 (growth or grow or grown or growing))) same (polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 15:23
S31	6515	((mono near2 (crystal or crystalline)) or monocrystalline or monocrystal or (single near2 (crystalline or crystal))) and (((silicon near2 (oxide or dioxide)) or "sio.sub.2" or sio2) same (sidewall or (side near2 wall))) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:15

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S32	8131	(((mono near2 (crystal or crystalline)) or monocrystalline or monocrystal or (single near2 (crystalline or crystal)) or epitaxially or epitaxial) with (silicon or si)) and (((silicon near2 (oxide or dioxide)) or "sio. sub.2" or sio2) same (sidewall or (side near2 wall))) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:15
S33	6048	S32 and S31	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:15
S34	6048	S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:15
S35	181	(((selective or selectively) near2 (epitaxial or epitaxy or epitaxially) near2 (grow or grown or growth or growing)) or SEG) and ((nonselectively or nonselective or differential or (non near selectively) or (non near selective)) near2 (epitaxial or epitaxy or epitaxially) near2 (grow or grown or growth or growing))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:19
S36	33	S32 and S35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:19
S37	42234	(((selective or selectively) near2 (epitaxial or epitaxy or epitaxially) near2 (grow or grown or growth or growing)) or SEG)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:24
S38	202	((nonselectively or nonselective or differential or (non near selectively) or (non near selective)) near2 (epitaxial or epitaxy or epitaxially) near2 (grow or grown or growth or growing))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:24
S39	1152	S32 and S37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:24
S40	33	S32 and S38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:24

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S41	75	((nonselectively or nonselective or differential or (non near selectively) or (non near selective)) near2 (epitaxial or epitaxy or epitaxially) near2 (grow or grown or growth or growing)) same (polysilicon or polycrystalline or amorphous))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:25
S42	9	S32 and S41	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 16:26
S43	8131	((mono near2 (crystal or crystalline)) or monocrystalline or monocrystal or (single near2 (crystalline or crystal)) or epitaxially or epitaxial) with (silicon or si)) and (((silicon near2 (oxide or dioxide)) or "sio. sub.2" or sio2) same (sidewall or (side near2 wall))) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 17:56
S44	8131	S43	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 17:56
S45	8311	438/309-378.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 17:56
S46	8311	S45	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 17:56
S47	326	S43 and S45	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 17:57
S48	11	S47 and ((salicide or salicidation) same (ti or titanium or co or cobalt or ni or nickel))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 17:58
S49	7986	HBT	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 18:04

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S50	3	S48 and S49	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 18:04
S51	275	S47 and ((phosphorous or p or arsenic) same (doping or doped or dopant or impurities or impurity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 18:09
S52	45	S51 and HBT	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 18:10
S53	277	S47 and ((phosphorous or phosphorus or p or arsenic) same (doping or doped or dopant or impurities or impurity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 18:16
S54	205	S47 and ((phosphorous or phosphorus or arsenic) same (doping or doped or dopant or impurities or impurity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 18:32
S55	31	S47 and ((phosphorous or phosphorus or arsenic) same (doping or doped or dopant or impurities or impurity)) and HBT	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 18:39
S56	8131	((mono near2 (crystal or crystalline)) or monocrystalline or monocrystal or (single near2 (crystalline or crystal)) or epitaxially or epitaxial) with (silicon or si)) and (((silicon near2 (oxide or dioxide)) or "sio. sub.2" or sio2) same (sidewall or (side near2 wall))) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 18:45
S57	8311	438/309-378.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 18:45
S58	326	S56 and S57	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/29 18:45
S59	37	S58 and ((Boron or b) same (doping or doped or dopant or impurities or impurity)) and HBT	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 18:45

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S60	27	S58 and ((Boron or b) same emitter same (doping or doped or dopant or impurities or impurity)) and HBT	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/29 18:47
S61	8143	((((mono near2 (crystal or crystalline)) or monocrystalline or monocrystal or (single near2 (crystalline or crystal)) or epitaxially or epitaxial) with (silicon or si)) and (((silicon near2 (oxide or dioxide)) or "sio.sub.2" or sio2) same (sidewall or (side near2 wall))) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 08:21
S62	8143	S61	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 08:21
S63	8312	438/309-378.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/30 08:22
S64	8311	S63	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 08:22
S65	42255	((selective or selectively) near2 (epitaxy or epitaxial or epitaxially) near2 (growing or grown or grow or growth)) or SEG)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 08:23
S66	973	((selective or selectively) near2 (epitaxy or epitaxial or epitaxially) near2 (growing or grown or grow or growth)) or SEG) same2 (sih2cl2 or "sih2.sub.2.cl.sub.2" or (sih2 near cl2) or ("sih.sub.2" near "cl.sub.2") or sih4 or silane or "sih.sub.4" or sicl4 or "sicl.sub.4" or sicl3 or "sicl.sub.3" or si2h6 or "si.sub.2.h.sub.6" or (si2 near h6) or ("si.sub.2" near "h.sub.6") or si3h8 or "si.sub.3.h.sub.8" or (si3 near h8) or ("si.sub.3" near "h.sub.8") or geh4 or "geh.sub.4" or sih3ch3 or "sih.sub.3.ch.sub.3" or ("sih.sub.3" near "ch.sub.3") or (sih3 near ch3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 08:28
S67	257	S61 and S66	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 08:29

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S68	16	S63 and S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 08:29
S69	15	S67 and hbt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 08:29
S70	7	S68 and hbt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 08:29
S71	8143	((mono near2 (crystal or crystalline)) or monocrystalline or monocrystal or (single near2 (crystalline or crystal)) or epitaxially or epitaxial) with (silicon or si)) and (((silicon near2 (oxide or dioxide)) or "sio. sub.2" or sio2) same (sidewall or (side near2 wall))) and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 11:51
S72	8143	S71	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 11:51
S73	8312	438/309-378.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/30 11:51
S74	8311	S73	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 11:51
S75	35	S72 and ((Boron or b) same (p near type) same emitter) and HBT	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2009/04/30 11:52